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Innovative Silicon's David Fisch to Present on Z-RAM[®] Memory Scalability at IWF IPT 2007

to 32nm and Beyond...

SANTA CLARA, Calif.,— Aug 24, 2007 — Innovative Silicon Inc.(ISi), the developer of Z-RAM[®] high-density memory intellectual property (IP), today announced that David Fisch, director of product architecture, will present a paper on Zero Capacitor RAM (Z-RAM) and its scalability path to 32-nm and beyond. The talk will take place at 11 a.m. on Wednesday, September 5, at the 7th International Workshop of Future Information Technology (IWF IPT) in Dresden, Germany, see <http://www.iwfip.t.gwtonline.de/> .

During the presentation, Fisch will discuss Z-RAM memory and its comparison to other embedded memories. Z-RAM technology harnesses the floating body effect of silicon on insulator (SOI) semiconductor devices and provides manufacturing advantages over standard bulk silicon memory technologies. It is ideal for Systems-on-Chip (SoC), microprocessors and portable consumer applications requiring low power, high density and high speed. Moreover, the technology has just been licensed by Hynix for use in future stand-alone DRAM chips. The discussion will also include an examination of Z-RAM memory cell features, as well as design and architectural considerations.

“With each new technology node, the challenges of building a robust, scaleable embedded memory grow and in turn drive higher process complexity and cost along with increased investments in capital equipment,” said Jeff Lewis, vice president of marketing, Innovative Silicon. “Despite these factors, the resulting memory macros reflect increasingly difficult trade-offs between power, speed and density. To effectively deal with these trends, today’s designers require a good understanding of the existing range of memory technologies, including Z-RAM, in order to make the optimal memory choice for any given application.”

About Innovative Silicon

Innovative Silicon Inc. (ISi) delivers ultra-high density memory IP for embedded SoC, MPU, stand-alone DRAM and portable consumer applications requiring low power, high density and high speed. Endorsed by IEEE Spectrum Magazine in January 2007 as the 'winning' semiconductor technology, and again in April 2007 by winning its ACE award for Emerging Technology, ISi's Z-RAM® memory offers up to twice the density of embedded DRAM and is up to five times denser than embedded SRAM. The company closed its first round of VC funding in 2003, completed its first 90nm megabit Z-RAM memory designs in 2004, its first 65nm designs in 2005 and its first 45nm designs in 2006. With more than 20 patents already granted, Z-RAM®'s unique single-transistor architecture is the world's lowest cost semiconductor memory solution. The company is incorporated in the USA with R&D in Lausanne, Switzerland. For more information see www.z-ram.com.

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